



®

Lyontek Inc.

LY61L20508A

Rev. 1.0

2048K X 8 BIT HIGH SPEED CMOS SRAM

REVISION HISTORY

<u>Revision</u>	<u>Description</u>	<u>Issue Date</u>
Rev. 1.0	Initial Issue	Jan.21.2014

FEATURES

- Fast access time : 10ns
- **Low power consumption:**
 Operating current:
 90mA (TYP.)
 Standby current:
 4mA (TYP.)
- Single 3.3V power supply
- All inputs and outputs TTL compatible
- Fully static operation
- Tri-state output
- Data retention voltage : 1.5V (MIN.)
- **Green package available**
- Package : 44-pin 400mil TSOP-II
 48-ball 6mm x 8mm TFBGA

GENERAL DESCRIPTION

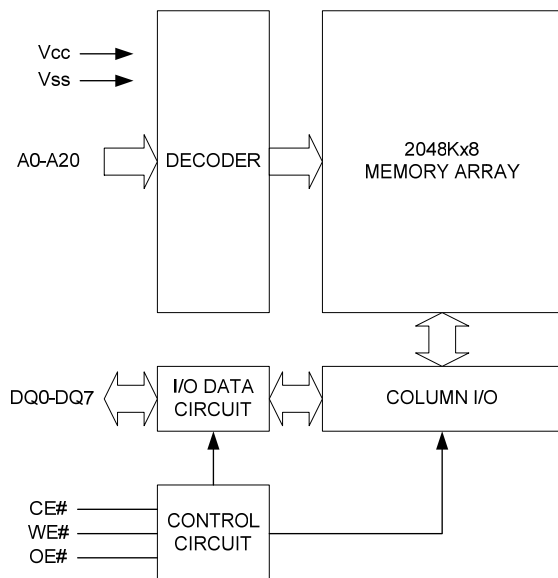
The LY61L20508A is a 16M-bit high speed CMOS static random access memory organized as 2048K words by 8 bits. It is fabricated using very high performance, high reliability CMOS technology. Its standby current is stable within the range of operating temperature.

The LY61L20508A operates from a single power supply of 3.3V and all inputs and outputs are fully TTL compatible

PRODUCT FAMILY

Product Family	Operating Temperature	V _{CC} Range	Speed	Power Dissipation	
				Standby(I _{SB1} , TYP.)	Operating(I _{CC} , TYP.)
LY61L20508A	0 ~ 70°C	2.7 ~ 3.6V	10ns	4mA	90mA
LY61L20508A(I)	-40 ~ 85°C	2.7 ~ 3.6V	10ns	4mA	90mA

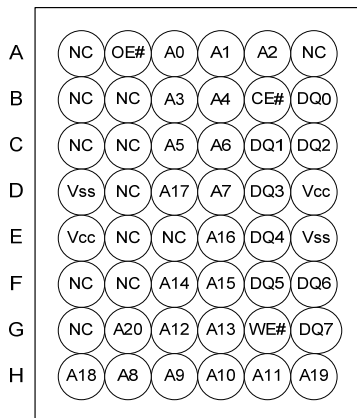
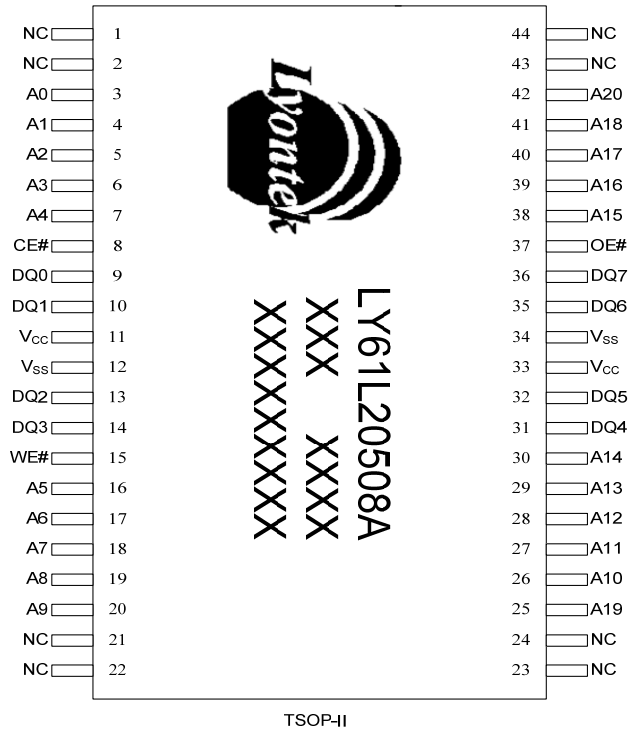
FUNCTIONAL BLOCK DIAGRAM



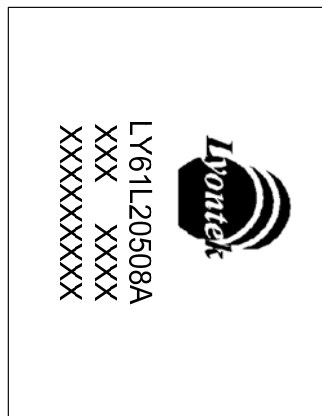
PIN DESCRIPTION

SYMBOL	DESCRIPTION
A0 - A20	Address Inputs
DQ0 - DQ7	Data Inputs/Outputs
CE#	Chip Enable Input
WE#	Write Enable Input
OE#	Output Enable Input
V _{CC}	Power Supply
V _{SS}	Ground

PIN CONFIGURATION



TFBGA(See through with Top View)



TFBGA(Top View)



ABSOLUTE MAXIMUM RATINGS*

PARAMETER	SYMBOL	RATING	UNIT
Voltage on V_{CC} relative to V_{SS}	V_{T1}	-0.5 to 4.6	V
Voltage on any other pin relative to V_{SS}	V_{T2}	-0.5 to $V_{CC}+0.5$	V
Operating Temperature	T_A	0 to 70(C grade)	°C
		-40 to 85(I grade)	
Storage Temperature	T_{STG}	-65 to 150	°C
Power Dissipation	P_D	1	W
DC Output Current	I_{OUT}	50	mA

*Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to the absolute maximum rating conditions for extended period may affect device reliability.

TRUTH TABLE

MODE	CE#	OE#	WE#	I/O OPERATION	SUPPLY CURRENT
Standby	H	X	X	High-Z	I_{SB1}
Output Disable	L	H	H	High-Z	I_{CC}
Read	L	L	H	D_{OUT}	I_{CC}
Write	L	X	L	D_{IN}	I_{CC}

Note: H = V_{IH} , L = V_{IL} , X = Don't care.

DC ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.*4	MAX.	UNIT
Supply Voltage	V_{CC}		2.7	3.3	3.6	V
Input High Voltage	V_{IH}^{*1}		2.2	-	$V_{CC}+0.3$	V
Input Low Voltage	V_{IL}^{*2}		-0.3	-	0.8	V
Input Leakage Current	I_{LI}	$V_{CC} \geq V_{IN} \geq V_{SS}$	-1	-	1	μA
Output Leakage Current	I_{LO}	$V_{CC} \geq V_{OUT} \geq V_{SS}$, Output Disabled	-1	-	1	μA
Output High Voltage	V_{OH}	$I_{OH} = -4mA$	2.4	-	-	V
Output Low Voltage	V_{OL}	$I_{OL} = 8mA$	-	-	0.4	V
Average Operating Power Supply Current	I_{CC}	CE# ≤ 0.2 , Others at 0.2V or $V_{CC}-0.2V$ $I_{IO} = 0mA; f = max$		90	120	mA
Standby Power Supply Current	I_{SB1}	CE# $\geq V_{CC} - 0.2V$, Others at 0.2V or $V_{CC} - 0.2V$	-	4	40	mA

Notes:

- $V_{IH}(max) = V_{CC} + 2.0V$ for pulse width less than 6ns.
- $V_{IL}(min) = V_{SS} - 2.0V$ for pulse width less than 6ns.
- Over/Undershoot specifications are characterized on engineering evaluation stage, not for mass production test.
- Typical values are included for reference only and are not guaranteed or tested.
Typical values are measured at $V_{CC} = V_{CC}(TYP.)$ and $T_A = 25^\circ C$

CAPACITANCE (T_A = 25°C, f = 1.0MHz)

PARAMETER	SYMBOL	MIN.	MAX	UNIT
Input Capacitance	C _{IN}	-	8	pF
Input/Output Capacitance	C _{I/O}	-	10	pF

Note : These parameters are guaranteed by device characterization, but not production tested.

AC TEST CONDITIONS

Speed	10ns
Input Pulse Levels	0.2V to V _{CC} - 0.2V
Input Rise and Fall Times	3ns
Input and Output Timing Reference Levels	V _{CC} /2
Output Load	C _L = 30pF + 1TTL, I _{OH} /I _{OL} = -4mA/8mA

AC ELECTRICAL CHARACTERISTICS
(1) READ CYCLE

PARAMETER	SYM.	LY61L20508A-10		UNIT
		MIN.	MAX.	
Read Cycle Time	t _{RC}	10	-	ns
Address Access Time	t _{AA}	-	10	ns
Chip Enable Access Time	t _{ACE}	-	10	ns
Output Enable Access Time	t _{OE}	-	4.5	ns
Chip Enable to Output in Low-Z	t _{CLZ} *	2	-	ns
Output Enable to Output in Low-Z	t _{OLZ} *	0	-	ns
Chip Disable to Output in High-Z	t _{CHZ} *	-	4	ns
Output Disable to Output in High-Z	t _{OHZ} *	-	4	ns
Output Hold from Address Change	t _{OH}	2	-	ns

(2) WRITE CYCLE

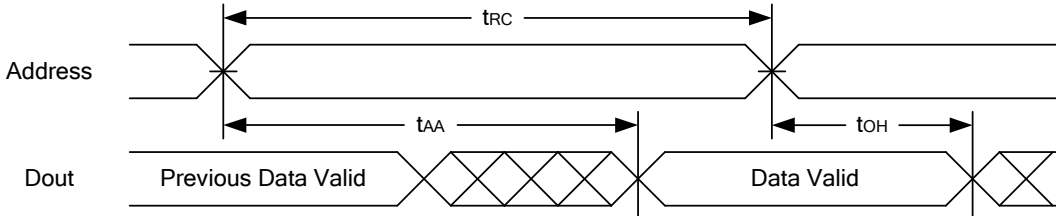
PARAMETER	SYM.	LY61L20508A-10		UNIT
		MIN.	MAX.	
Write Cycle Time	t _{WC}	10	-	ns
Address Valid to End of Write	t _{AW}	8	-	ns
Chip Enable to End of Write	t _{CW}	8	-	ns
Address Set-up Time	t _{AS}	0	-	ns
Write Pulse Width	t _{WP}	8	-	ns
Write Recovery Time	t _{WR}	0	-	ns
Data to Write Time Overlap	t _{DW}	6	-	ns
Data Hold from End of Write Time	t _{DH}	0	-	ns
Output Active from End of Write	t _{OW} *	2	-	ns
Write to Output in High-Z	t _{WHZ} *	-	4	ns

*These parameters are guaranteed by device characterization, but not production tested.

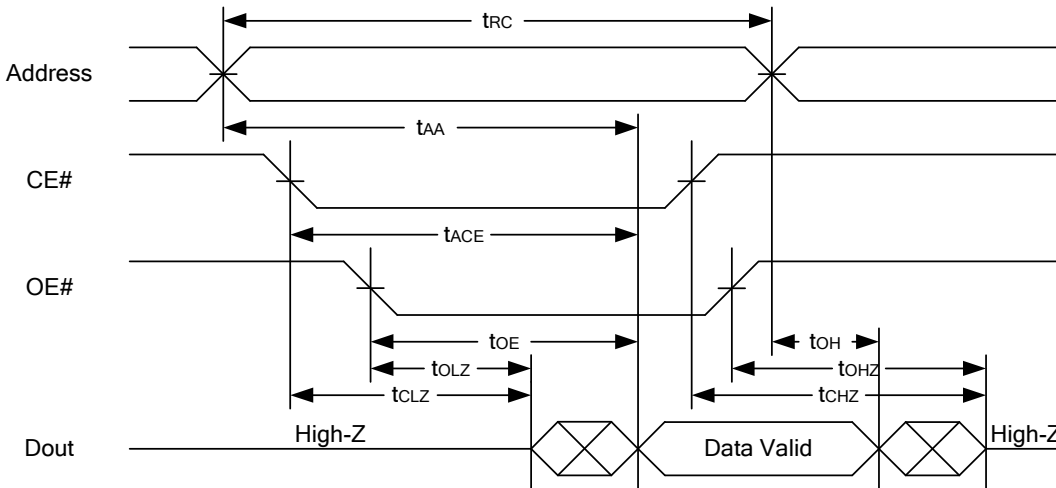


TIMING WAVEFORMS

READ CYCLE 1 (Address Controlled) (1,2)



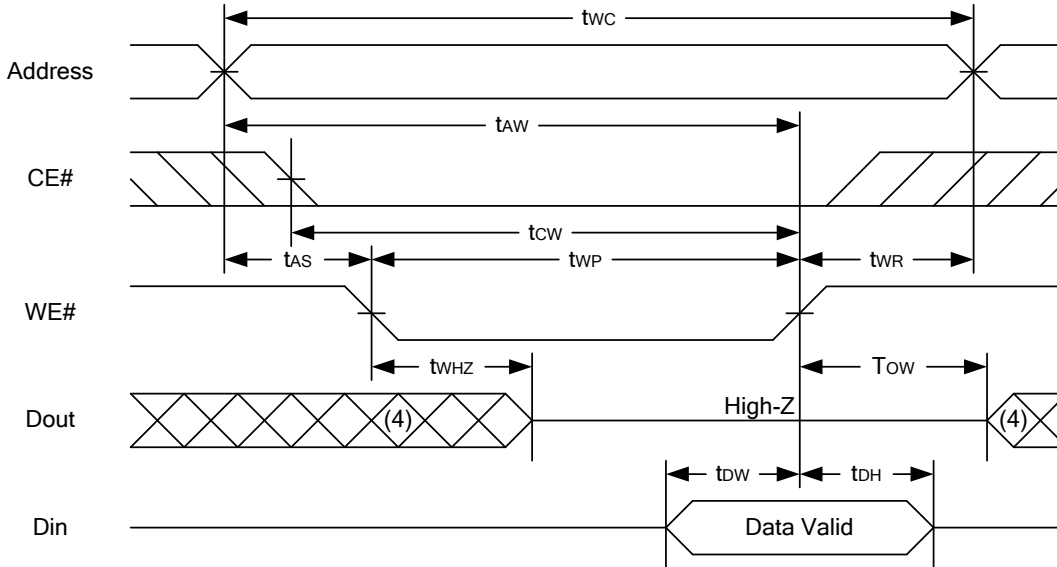
READ CYCLE 2 (CE# and OE# Controlled) (1,3,4,5)



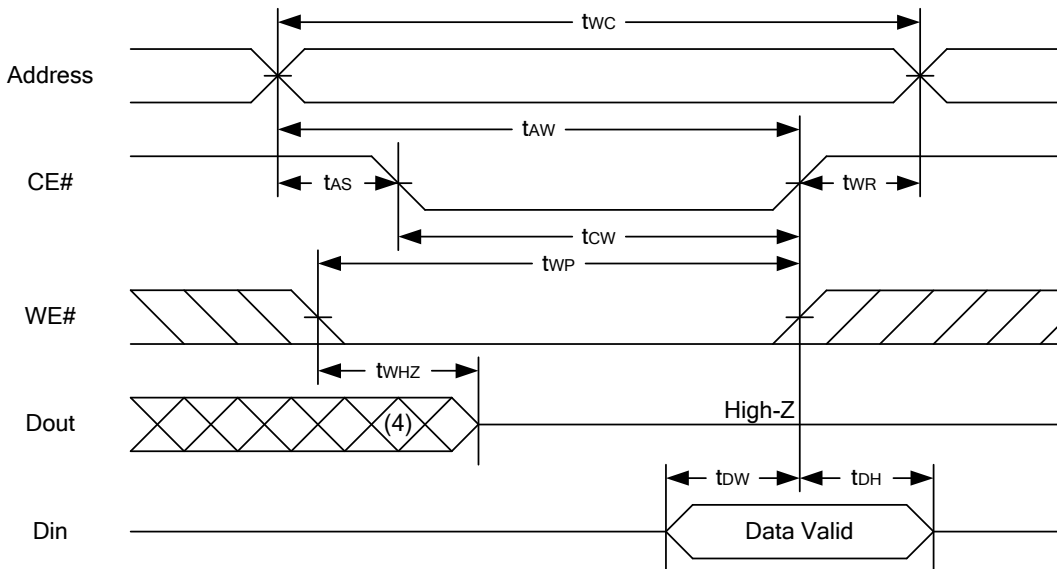
Notes :

1. WE# is high for read cycle.
2. Device is continuously selected OE# = low, CE# = low.
3. Address must be valid prior to or coincident with CE# = low,; otherwise t_{AA} is the limiting parameter.
4. t_{CLZ} , t_{OLZ} , t_{CHZ} and t_{OHZ} are specified with $C_L = 5\text{pF}$. Transition is measured $\pm 500\text{mV}$ from steady state.
5. At any given temperature and voltage condition, t_{CHZ} is less than t_{CLZ} , t_{OHZ} is less than t_{OLZ} .

WRITE CYCLE 1 (WE# Controlled) (1,2,3,5,6)



WRITE CYCLE 2 (CE# Controlled) (1,2,5,6)



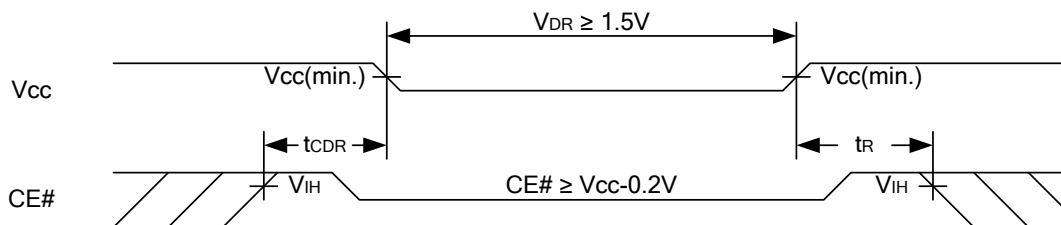
Notes :

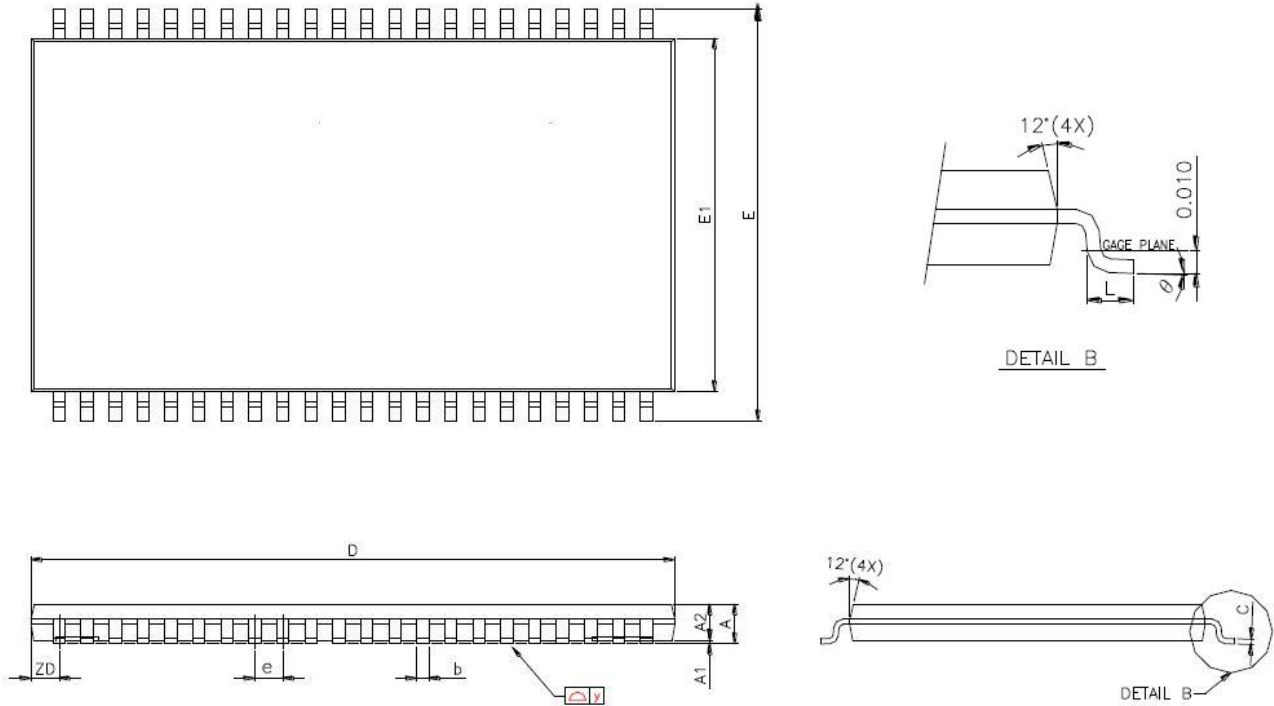
1. WE#, CE#, LB#, UB# must be high during all address transitions.
2. A write occurs during the overlap of a low CE#, low WE#, LB# or UB# = low.
3. During a WE# controlled write cycle with OE# low, tWP must be greater than tWHZ + tDW to allow the drivers to turn off and data to be placed on the bus.
4. During this period, I/O pins are in the output state, and input signals must not be applied.
5. If the CE#, LB#, UB# low transition occurs simultaneously with or after WE# low transition, the outputs remain in a high impedance state.
6. tOW and tWHZ are specified with CL = 5pF. Transition is measured ±500mV from steady state.

DATA RETENTION CHARACTERISTICS

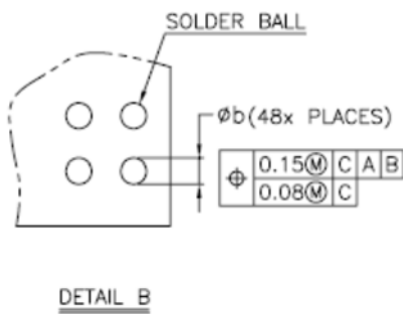
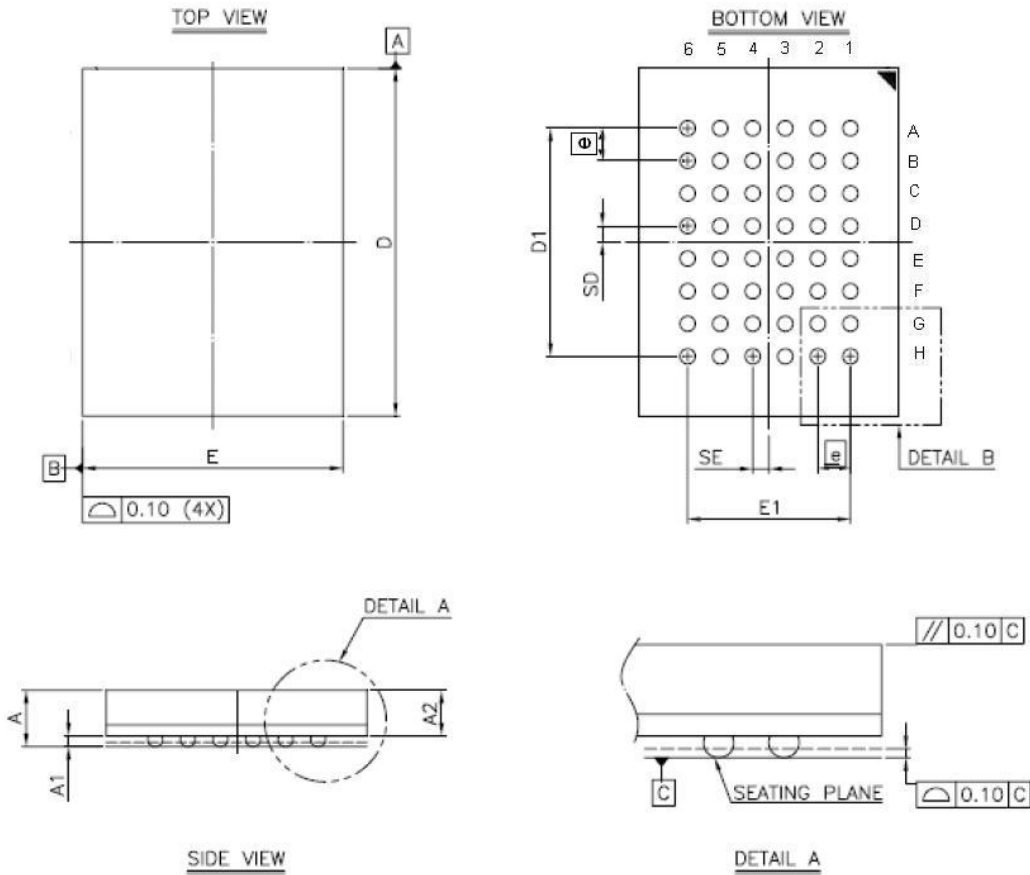
PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
V _{CC} for Data Retention	V _{DR}	CE# ≥ V _{CC} - 0.2V	1.5	-	3.6	V
Data Retention Current	I _{DR}	V _{CC} = 1.5V CE# ≥ V _{CC} - 0.2V Others at 0.2V or V _{CC} - 0.2V	-	4	40	mA
Chip Disable to Data Retention Time	t _{CDR}	See Data Retention Waveforms (below)	0	-	-	ns
Recovery Time	t _R		t _{RC} *	-	-	ns

 t_{RC}* = Read Cycle Time

DATA RETENTION WAVEFORM


PACKAGE OUTLINE DIMENSION
44-pin 400mil TSOP-II Package Outline Dimension


SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN MILS		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	-	-	1.20	-	-	47.2
A1	0.05	0.10	0.15	2.0	3.9	5.9
A2	0.95	1.00	1.05	37.4	39.4	41.3
b	0.30	-	0.45	11.8	-	17.7
c	0.12	-	0.21	4.7	-	8.3
D	18.212	18.415	18.618	717	725	733
E	11.506	11.760	12.014	453	463	473
E1	9.957	10.160	10.363	392	400	408
e	-	0.800	-	-	31.5	-
L	0.40	0.50	0.60	15.7	19.7	23.6
ZD	-	0.805	-	-	31.7	-
y	-	-	0.076	-	-	3
θ	0°	3°	6°	0°	3°	6°

48-ball 6mm × 8mm TFBGA Package Outline Dimension


SYM.	DIMENSION (mm)			DIMENSION (inch)		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	—	—	1.40	—	—	0.055
A1	0.20	0.25	0.30	0.008	0.010	0.012
A2	—	—	1.05	—	—	0.041
b	0.30	0.35	0.40	0.012	0.014	0.016
D	7.95	8.00	8.05	0.313	0.315	0.317
D1	5.25 BSC			0.207 BSC		
E	5.95	6.00	6.05	0.234	0.236	0.238
E1	3.75 BSC			0.148 BSC		
SE	0.375 TYP			0.015 TYP		
SD	0.375 TYP			0.015 TYP		
	0.75 BSC			0.030 BSC		

NOTE:

1. CONTROLLING DIMENSION : MILLIMETER.
2. REFERENCE DOCUMENT : JEDEC MO-207.



ORDERING INFORMATION

Package Type	Access Time (Speed/ns)	Temperature Range(°C)	Packing Type	Lyontek Item No.
44-Pin 400mil TSOP-II	10	0°C~70°C	Tray	LY61L20508AML-10
			Tape Reel	LY61L20508AML-10T
		-40°C~85°C	Tray	LY61L20508AML-10I
			Tape Reel	LY61L20508AML-10IT
48-Ball 6mm x 8mm TFBGA	10	0°C~70°C	Tray	LY61L20508AGL-10
			Tape Reel	LY61L20508AGL-10T
		-40°C~85°C	Tray	LY61L20508AGL-10I
			Tape Reel	LY61L20508AGL-10IT



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